

## Silicon Schottky Diode

## BAT68-04W, BAT68-05W, BAT68-06W

## ■ Features

- For mixer applications in VHF/UHF range
- For high-speed switching application

■ Absolute Maximum Ratings  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Value	Unit
Diode reverse voltage	$V_R$	8	V
Forward current	$I_F$	130	mA
Total power dissipation	$P_{tot}$	150	mW
Junction temperature	$T_j$	150	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-55 to +150	$^\circ\text{C}$
Junction - soldering point(Note 1)	$R_{thJS}$	$\leq 390$	K/W

Note

1.For calculation of  $R_{thJA}$  please refer to Application Note Thermal Resistance■ Electrical Characteristics  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Breakdown voltage	$V_{(BR)}$	$I_{(BR)} = 10 \mu\text{A}$	8			V
Reverse current	$I_R$	$V_R = 1\text{V}$			0.1	$\mu\text{A}$
		$V_R = 1\text{V}, T_A = 60^\circ\text{C}$			1.2	
Forward voltage	$V_F$	$I_F = 1\text{mA}$		318	340	mV
		$I_F = 10\text{mA}$	340	390	500	
Diode capacitance	$C_T$	$V_R = 0, f = 1\text{MHz}$			1	pF
Differential forward resistance	$R_F$	$I_F = 5\text{mA}, f = 10\text{KHz}$			10	$\Omega$

## ■ Marking

Type	BAT68-04W	BAT68-05W	BAT68-06W
Marking	84s	85s	86s

